

# **Excellent Integrated System Limited**

Stocking Distributor

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Rohm Semiconductor 2SK2713

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### Transistors

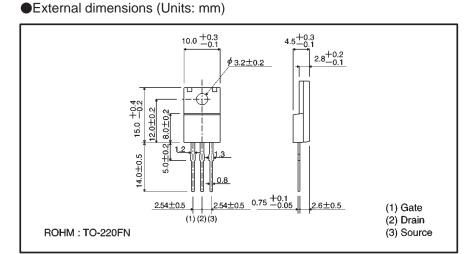
# Switching (450V, 5A) 25K2713

#### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- Gate-source voltage (V<sub>GSS</sub>) guaranteed to be ±30V.
- 5) Easily designed drive circuits.
- 6) Easy to parallel.

#### Structure

Silicon N-channel MOSFET



## • Absolute maximum ratings (Ta = $25^{\circ}$ C)

Parameter		Symbol	Limits	Unit
Falameter	Farameter Sy		Linnto	Unit
Drain-source voltage		VDSS	450	V
Gate-source voltage		Vgss	±30	V
Designment	Continuous	D	5	А
Drain current	Pulsed	DP*	20	А
Reverse drain	Continuous	DR	5	А
current	Pulsed	IDRP*	20	А
Total power dissipation (Tc=25°C)		PD	30	W
Channel temperature		Tch	150	Ĉ
Storage temperature	ıre Tstg −55~+150 ℃		ĉ	

\*  $Pw \leq 10 \mu s$ , Duty cycle  $\leq 1\%$ 

#### Packaging specifications

	Package	Bulk
Туре	Code	—
	Basic ordering unit (pieces)	500
2SK2713		0



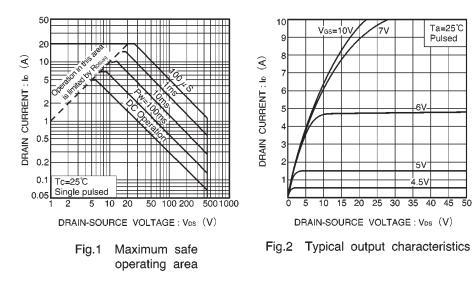
Transistors

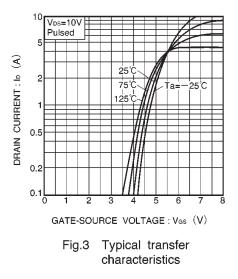
2SK2713

Electrical characteristics	(Ta = 25°C)
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Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Gate-source leakage	lass			±100	nA	$V_{GS}=\pm 30V$ , $V_{DS}=0V$
Drain-source breakdown voltage	V(BR)DSS	450	_	_	V	ID=1mA, VGS=0V
Zero gate voltage drain current	loss	_	_	100	μA	V <sub>DS</sub> =450V, V <sub>GS</sub> =0V
Gate threshold voltage	VGS(th)	2.0	_	4.0	V	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
Static drain-source on-state resistance	RDS(on)	_	1.0	1.4	Ω	ID=2.5A, VGS=10V
Forward transfer admittance	Y <sub>fs</sub>	1.0	3.0	_	S	ID=2.5A, VDS=10V
Input capacitance	Ciss		600	_	pF	V <sub>DS</sub> =10V
Output capacitance	Coss	_	135	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss		53	_	pF	f=1MHz
Turn-on delay time	td(on)		14	_	ns	I□=2.5A, V□□≑150V
Rise time	tr		17	_	ns	V <sub>GS</sub> =10V
Turn-off delay time	td(off)		50	_	ns	R∟=60Ω
Fall time	tr		35	_	ns	Rg=10Ω
Reverse recovery time	trr		300	—	ns	IDR=5A, VGS=0V
Reverse recovery charge	Qrr		1.8	_	μC	di/dt=100A/μs

Electrical characteristic curves





Ta=25°C Pulsed

45

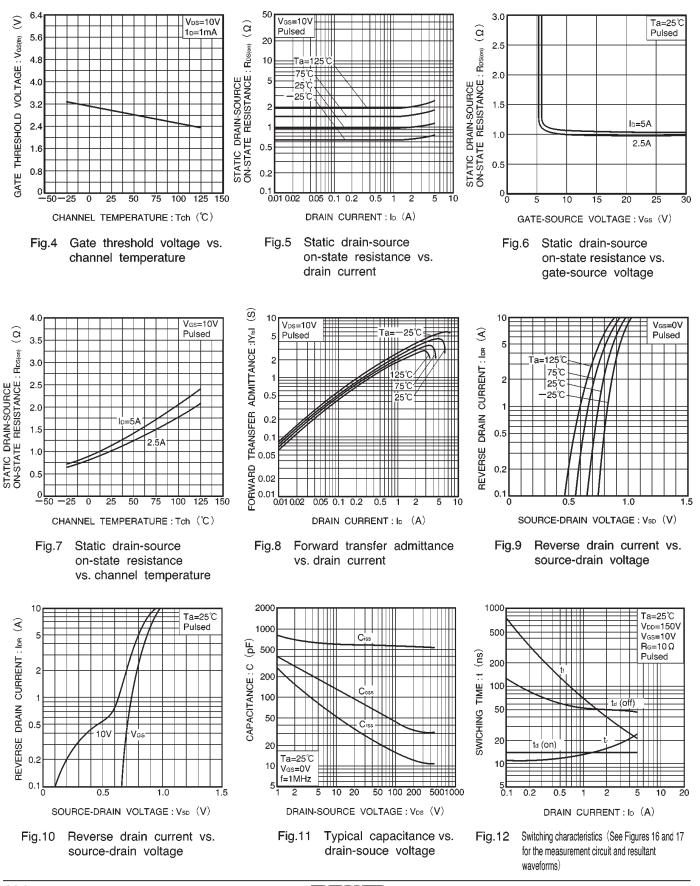
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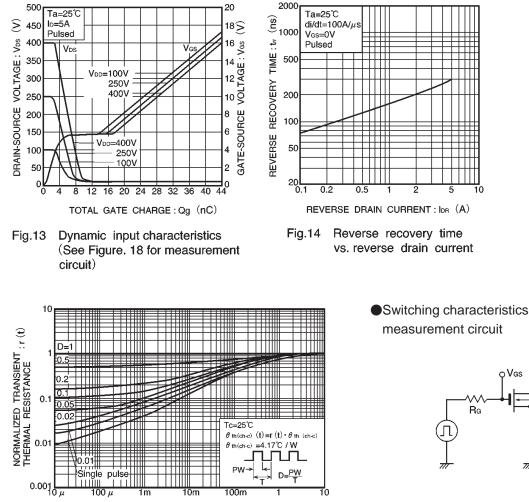


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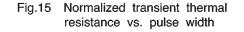


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PULSE WIDTH : PW (s)



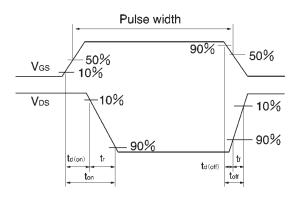


Fig.17 Switching time waveforms

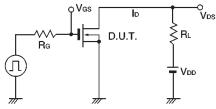


Fig.16 Switching time measurement circuit

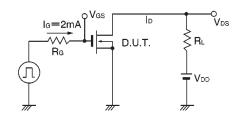


Fig.18 Gate charge measurement circuit



# Appendix

#### Notes

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